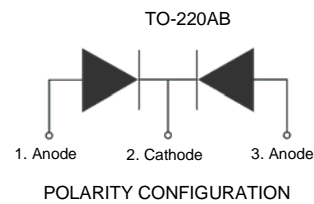
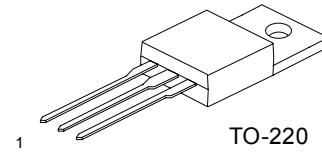




10A SCHOTTKY BARRIER DIODE Dual High Voltage Schottky Rectifier

Specification Features:

- High Voltage Wide Range Selection, 100V, 150V & 200V
- High Switching Speed Device
- Low Forward Voltage Drop
- Low Power Loss and High Efficiency
- Guard Ring for Over-voltage Protection
- High Surge Capability
- RoHS Compliant
- Matte Tin(Sn) Lead Finish
- Terminal Leads Surface is Corrosion Resistant and can withstand to 260°C Wave Soldering or per MIL-STD-750, Method 2026.



DEVICE MARKING DESIGNATION:
Line 1 & 2= Device Name
Line 3 = Datecode
Line 4 = Polarity

MAXIMUM RATINGS (Per Leg, unless otherwise specified)

Symbol	Parameter	MBR10100CT	MBR10150CT	MBR10200CT	Units
V_{RRM} V_{RWM} V_R	Maximum Repetitive Reverse Voltage Working Peak Reverse Voltage Maximum DC Reverse Voltage	100	150	200	V
$I_{F(AV)}$	Average Rectified Forward Current Per Leg Per Package	5 10			A
I_{FSM}	Non-repetitive Peak Forward Surge Current 8.3mS Single Phase @ Rated Load	80			A
T_{STG}	Storage Temperature Range	-65 to +175			°C
T_J	Operating Junction Temperature	+175			°C

These ratings are limiting values above which the serviceability of the diode may be impaired.

THERMAL CHARACTERISTIC

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Maximum Thermal Resistance, Junction-to-Case	1.5	°C/W

ELECTRICAL CHARACTERISTICS (Per Leg) $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition (Note 1)	MBR10100CT		MBR10150CT		MBR10200CT		Units
			Min	Max	Min	Max	Min	Max	
I_R	Reverse Current	@ rated V_R	---	100	---	100	---	100	μA
V_F	Forward Voltage	$I_F = 5\text{A}$	---	0.850	---	0.900	---	0.950	V
		$I_F = 10\text{A}$	---	0.900	---	0.950	---	1	

Note/s:

1. Tested under pulse condition of 300 μs .